

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a ferroelectric capacitor, comprising:

forming a lower electrode on a ~~base~~substrate;

forming a ferroelectric film which includes a lead zirconate titanate niobate (PZTN) complex oxide including lead, zirconium, titanium, and niobium on the lower electrode;

forming an upper electrode on the ferroelectric film;

forming a ~~protective~~silicon oxide film ~~without providing a hydrogen barrier film~~ so as to cover the lower electrode, the ferroelectric film, and the upper electrode; and

performing heat treatment for crystallizing the PZTN complex oxide at least after forming the ~~protective~~silicon oxide film.

2. (Currently Amended) The method of manufacturing a ferroelectric capacitor as defined in claim 1,

~~wherein~~ the PZTN complex oxide ~~is~~being in an amorphous state after pre-heat treatment in an oxidizing atmosphere and before the heat treatment in the step of forming the ferroelectric film.

3. (Currently Amended) The method of manufacturing a ferroelectric capacitor as defined in claim 1,

~~wherein the protective film is a silicon oxide film and~~the silicon oxide film is~~being~~ formed by using trimethylsilane.

4. (Currently Amended) The method of manufacturing a ferroelectric capacitor as defined in claim 1,

~~wherein~~ the heat treatment for crystallizing the PZTN complex oxide ~~is~~ being performed in a non-oxidizing atmosphere.

5.-7. (Canceled)